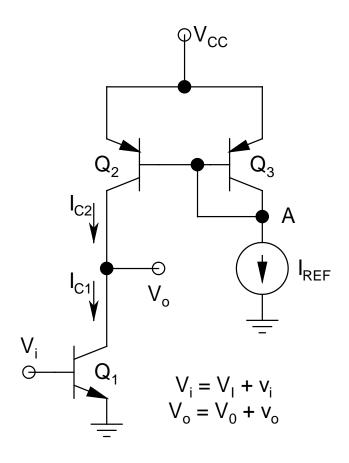
• npn CE Stage With pnp Active Load:

- \triangleright Q₁: *Driver*, Q₂: *Load*
- ► Identify Q_2 - Q_3 as a pnp current mirror
- ➤ Q₂-Q₃ constitute a *matched pair*
- > Neglecting base currents: $I_{C2} = I_{REF}$
- ➤ Biasing of the circuit is tricky



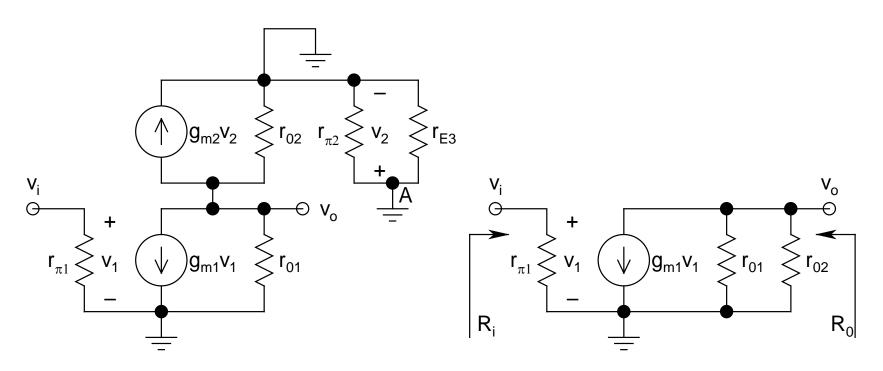
Circuit Diagram

- There is a *trivial solution* of $I_{C1} = I_{C2} = 0$, and the *circuit collapses*
- \succ For proper biasing, I_{C1} must equal I_{C2} (= I_{REF})
- Thus, V_I should be properly adjusted, such that:

$$V_I = V_T ln(I_{REF}/I_{S1})$$

- \succ Such a high precision in V_I may not be practically achievable
 - \Rightarrow Use a resistor in series with V_I and self-consistently solve for the bias point

> ac Analysis:



ac Midband Equivalent

Simplified Equivalent

- First, note that Q_3 is *diode-connected* (*BC short*)

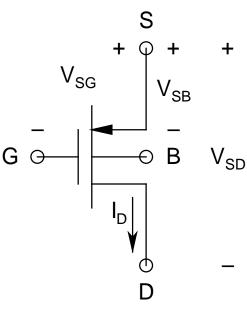
 ⇒ The *equivalent* of Q_3 is simply a *resistor* r_{E3}
- Node A is a peculiar one, and can be considered open or short both!
 - riangle Open because the current source I_{REF} is ideal
 - \Leftrightarrow Short because the base of Q_2 - Q_3 is at a fixed DC potential, and thus ac ground
- In either case, $v_2 = 0 \Rightarrow g_{m2}v_2$ disappears! ⇒ Leads to the simplified equivalent
- **By inspection**: $R_i = r_{\pi 1}$ and $R_0 = r_{01} || r_{02}$
- $A_v = v_o/v_i = -g_{m1}R_0 = -1/(\eta_n + \eta_p)$ $\eta_n = V_T/V_{AN} \text{ and } \eta_p = V_T/V_{AP}$
- Enormously large gain possible!

p-channel MOSFET (PMOS)

- Before moving to *NMOS stages with active load*, it will be prudent to visit some details regarding *PMOS*
- Substrate: n-type (N_D)
 - > Bulk Potential:

$$\phi_F = V_T ln(N_D/n_i)$$

- Source/Drain: p+
- Channel Carriers: Holes



PMOS